

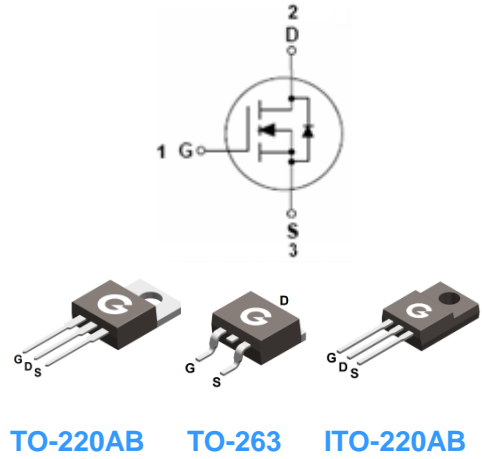
Features

- Low power loss by high speed switching and low on-resistance
- Excellent thermal behavior
- Product validation acc. JEDEC Standard
- RoHS compliant with Halogen-free

HF

Mechanical Data

- Case: TO-220AB, TO-263, ITO-220AB
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



Ordering Information

| Part Number | Package | Shipping Quantity | Marking Code |
|-------------|-----------|--|--------------|
| SJM60R600X | TO-220AB | 50 pcs / Tube | SJM60R600X |
| SJM60R600XB | TO-263 | 50 pcs / Tube or 800 pcs / Tape & Reel | SJM60R600XB |
| SJM60R600XF | ITO-220AB | 50 pcs / Tube | SJM60R600XF |

Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|---|-----------|------------|------------------|
| Drain-to-Source Voltage | V_{DSS} | 600 | V |
| Gate-to-Source Voltage | V_{GSS} | ± 30 | V |
| Continuous Drain Current ($T_C = 25^\circ\text{C}$) | I_D | 8 | A |
| Continuous Drain Current ($T_C = 100^\circ\text{C}$) | | 5 | A |
| Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_C = 25^\circ\text{C}$) | I_{DM} | 32 | A |
| Single Pulse Avalanche Energy ² | E_{AS} | 200 | mJ |
| Power Dissipation (TO-220AB, $T_C = 25^\circ\text{C}$) | P_D | 63 | W |
| Power Dissipation (TO-263, $T_C = 25^\circ\text{C}$) | | 63 | W |
| Power Dissipation (ITO-220AB, $T_C = 25^\circ\text{C}$) | | 26 | W |
| Operating Junction Temperature Range | T_J | -55 ~ +150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{STG} | -55 ~ +150 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | TO-220AB/TO-263 | ITO-220AB | Unit |
|-------------------------------------|-----------------|-----------------|-----------|--------------------|
| Thermal Resistance Junction-to-Case | $R_{\theta JC}$ | 2 | 4.8 | $^\circ\text{C/W}$ |
| Thermal Resistance Junction-to-Air | $R_{\theta JA}$ | 62 | 75 | $^\circ\text{C/W}$ |

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Unit |
|---|---------------------------------|--|------|------|-----------|----------|
| Static Characteristics | | | | | | |
| V_{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = 250\mu A$ | 600 | - | - | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 600V, V_{GS} = 0V$ | - | - | 1 | μA |
| I_{GSS} | Gate-Body Leakage Current | $V_{GS} = \pm 30V, V_{DS} = 0V$ | - | - | ± 100 | nA |
| On Characteristics | | | | | | |
| $R_{DS(ON)}$ | Drain-Source On-resistance *1 | $V_{GS} = 10V, I_D = 4A$ | - | 0.45 | 0.6 | Ω |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 2.5 | 3.3 | 4.5 | V |
| R_G | Gate Resistance | $V_{GS} = 0V, f = 1MHz$ | - | 12 | - | Ω |
| Dynamic Characteristics | | | | | | |
| C_{ISS} | Input Capacitance | $V_{GS} = 0V$ $V_{DS} = 40V$ $f = 250kHz$ | - | 408 | - | μF |
| C_{OSS} | Output Capacitance | | - | 88 | - | |
| C_{RSS} | Reverse Transfer Capacitance | | - | 6.5 | - | |
| Switching Characteristics | | | | | | |
| $t_{d(ON)}$ | Turn-on Delay Time | $V_{DD} = 480V$ $V_{GS} = 15V$ $I_D = 4A$ $R_G = 3.3\Omega$ | - | 25 | - | ns |
| t_r | Turn-on Rise Time | | - | 33 | - | |
| $t_{d(OFF)}$ | Turn-Off Delay Time | | - | 40 | - | |
| t_f | Turn-Off Fall Time | | - | 66 | - | |
| Q_G | Total Gate-Charge | $V_{DD} = 480V$ $V_{GS} = 10V$ $I_D = 4A$ | - | 16.4 | - | nC |
| Q_{GS} | Gate to Source Charge | | - | 2.3 | - | |
| Q_{GD} | Gate to Drain (Miller) Charge | | - | 9.2 | - | |
| Source-Drain Diode Characteristics | | | | | | |
| V_{SD} | Diode Forward Voltage *1 | $I_{SD} = 4A, V_{GS} = 0V$ | - | 0.82 | 1.2 | V |
| t_{rr} | Reverse Recovery Time | $I_F = 4A, V_R = 400V$ $di/dt = 100A/\mu s$ | - | 230 | - | ns |
| Q_{rr} | Reverse Recovery Charge | | - | 1.7 | - | μC |

Notes:

- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 100V, V_{GS} = 15V, L = 50mH$

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

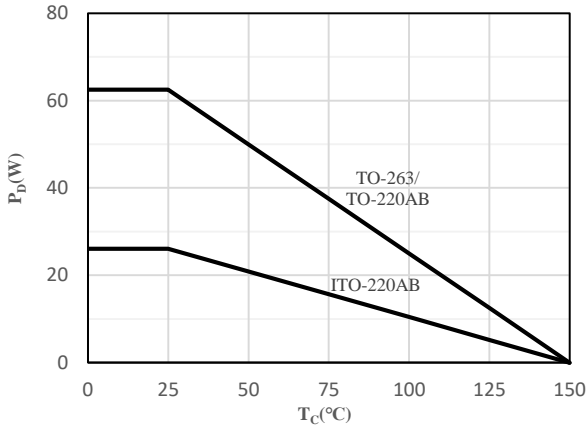


Fig 1 Power Dissipation

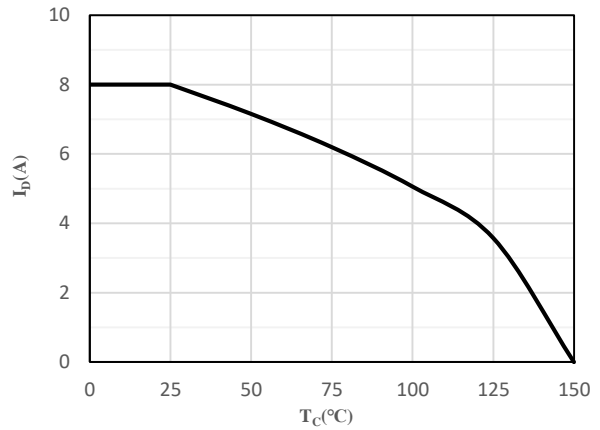


Fig 2 Drain Current

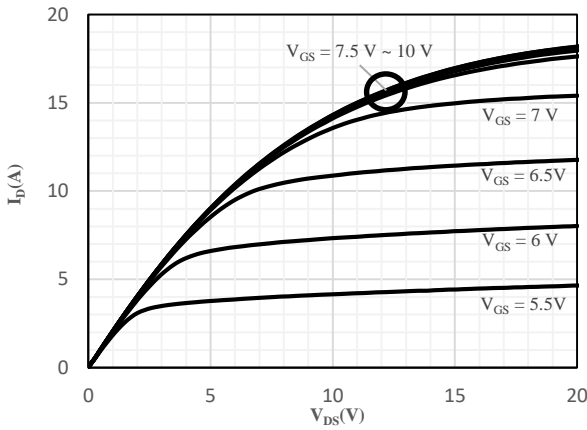


Fig 3 Typical Output Characteristics

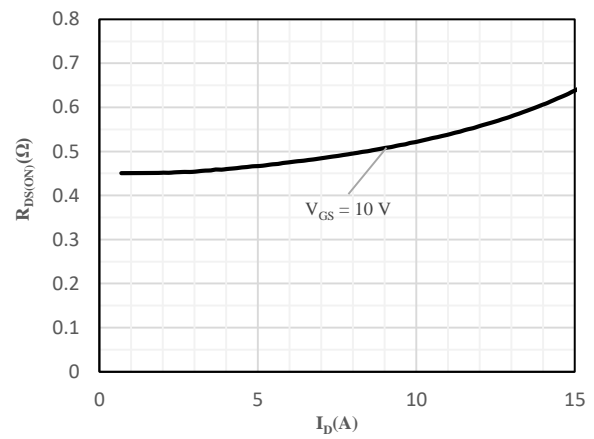


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

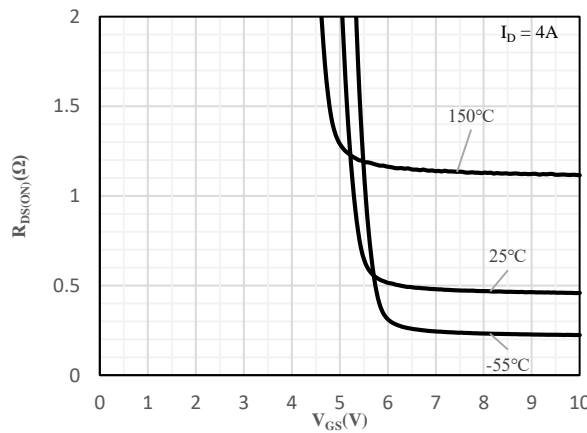


Fig 5 On-Resistance vs. Gate-Source Voltage

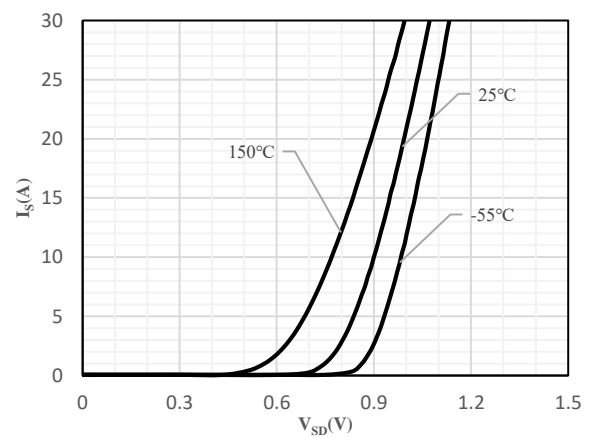


Fig 6 Body-Diode Characteristics

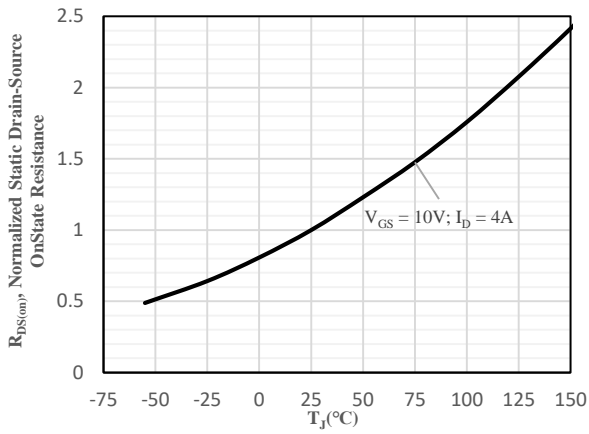


Fig 7 Normalized On-Resistance vs. Junction Temperature

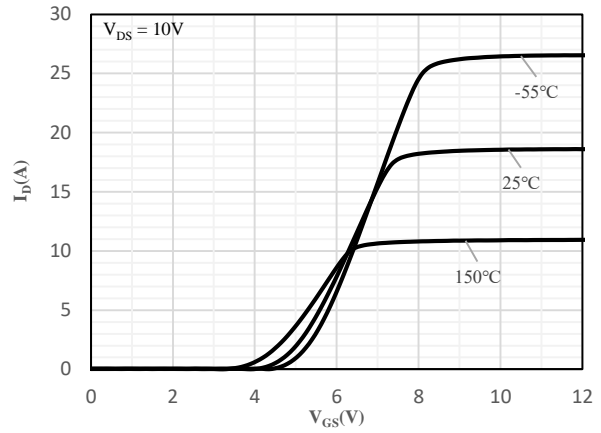


Fig 8 Transfer Characteristics

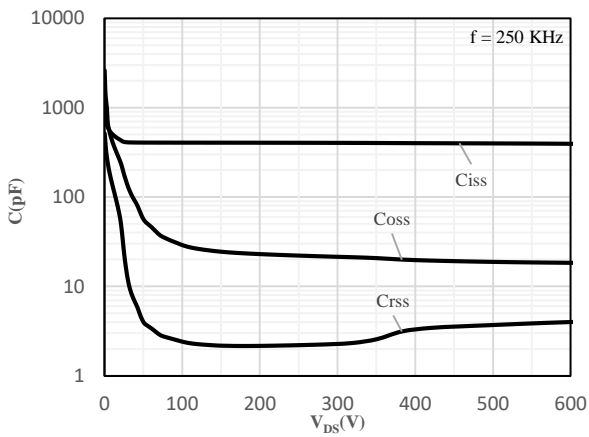


Fig 9 Capacitance Characteristics

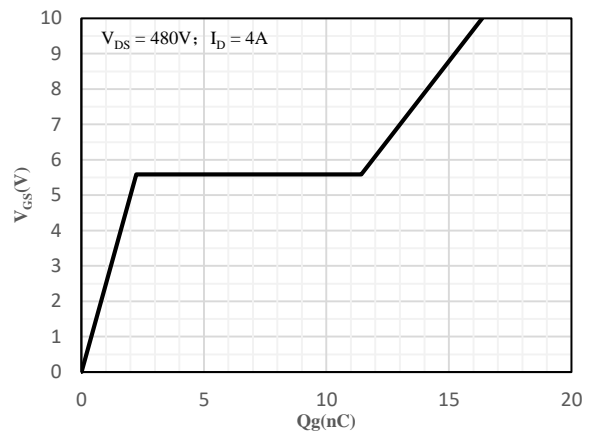


Fig 10 Gate-Charge Characteristics

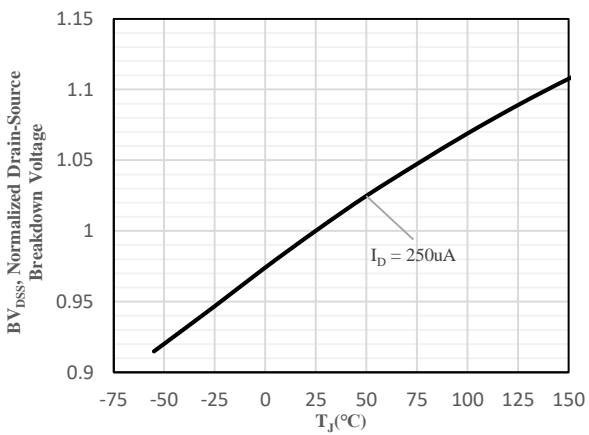


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

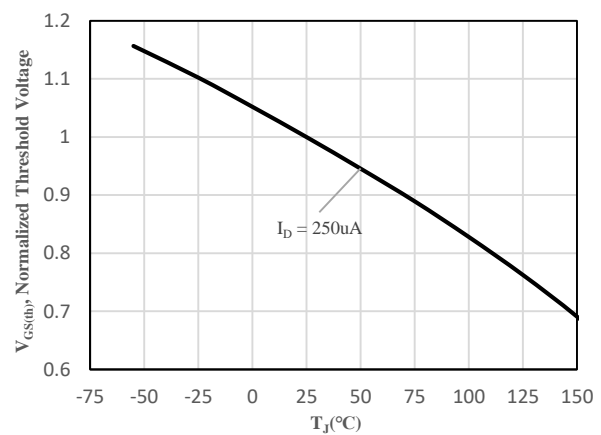


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

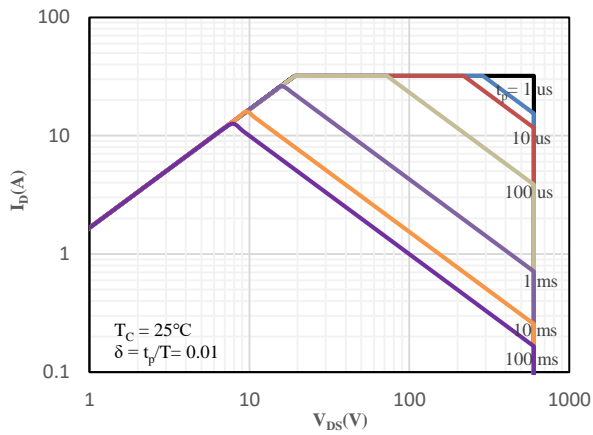


Fig 13 Safe Operation Area (TO-220AB / TO-263)

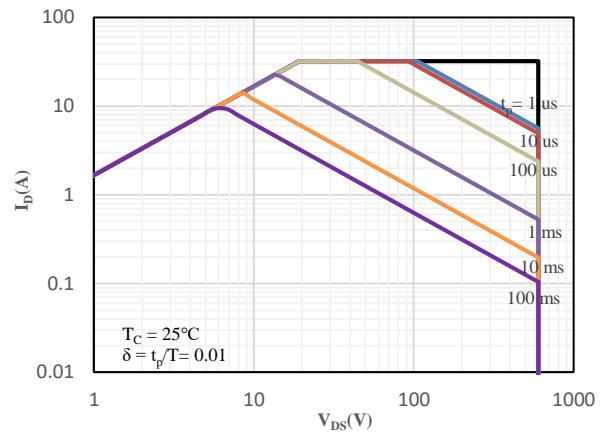


Fig 14 Safe Operation Area (ITO-220AB)

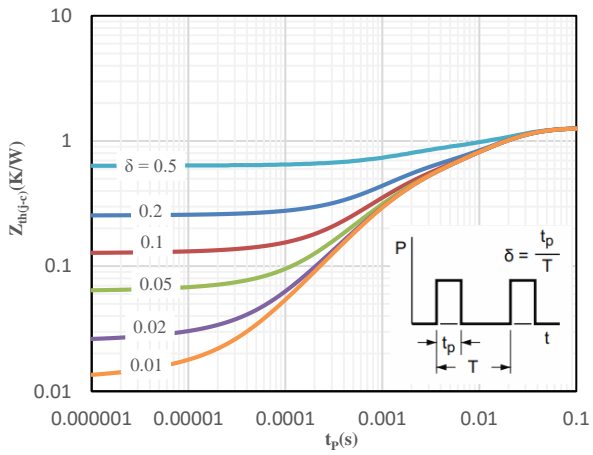


Fig 15 Maximum transient thermal impedance (TO-220AB / TO-263)

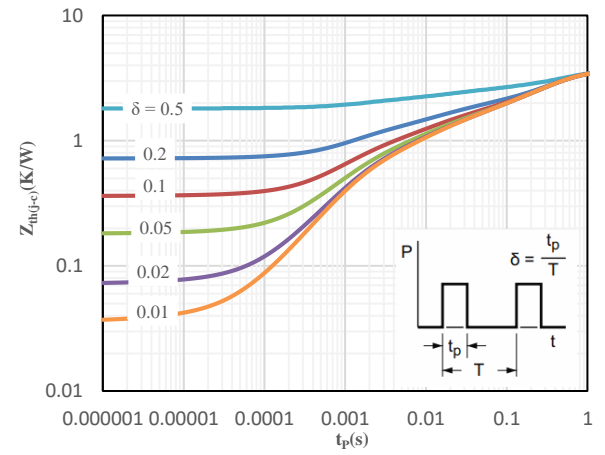
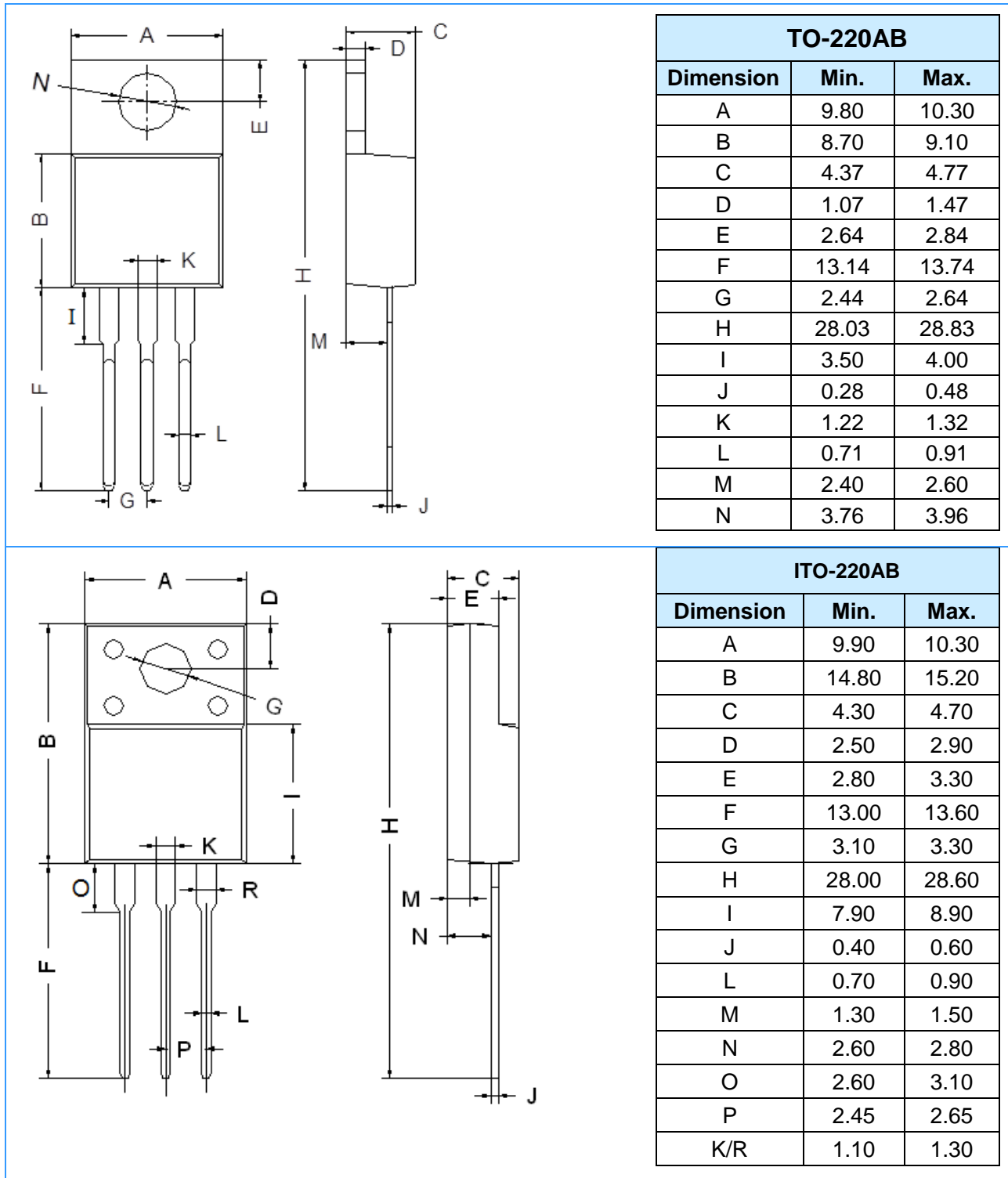
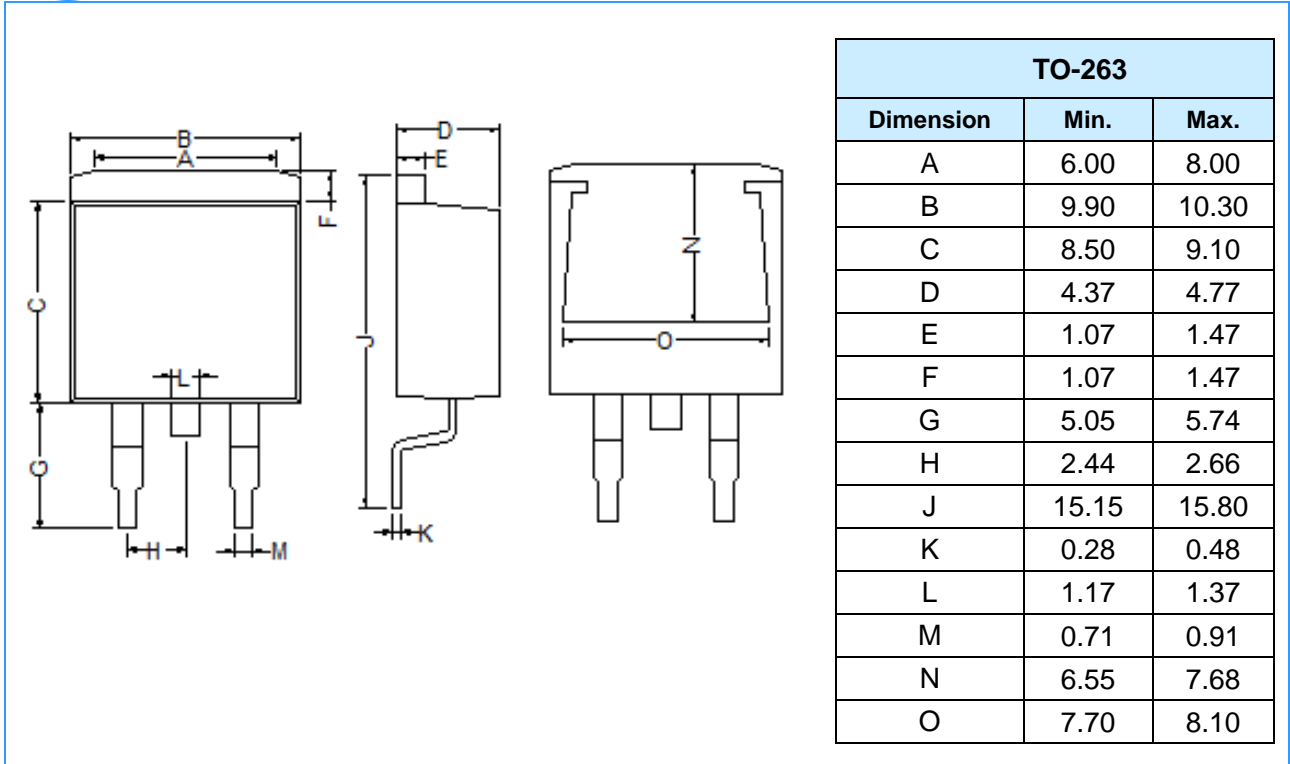


Fig 16 Maximum transient thermal impedance (ITO-220AB)

Package Outline Dimensions (Unit: mm)





Mounting Pad Layout (Unit: mm)

